

Atsushi Kawaharazuka

List of Publications by Year in descending order

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27
papers

155
citations

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28
all docs

28
docs citations

28
times ranked

168
citing authors

#	ARTICLE	IF	CITATIONS
1	Spin-Polarized Electron Injection through an Fe/InAs Junction. Japanese Journal of Applied Physics, 2003, 42, L87-L89.	1.5	20
2	Formation of a two-dimensional electron gas in an inverted undoped heterostructure with a shallow channel depth. Journal of Applied Physics, 2000, 87, 952-954.	2.5	15
3	MBE growth of GaN on MgO substrate. Journal of Crystal Growth, 2007, 301-302, 478-481.	1.5	12
4	Successful growth of Cu ₂ Se-free CuGaSe ₂ by migration-enhanced epitaxy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, .	1.2	10
5	Investigation of CuGaSe ₂ /CuInSe ₂ double heterojunction interfaces grown by molecular beam epitaxy. AIP Advances, 2015, 5, 027120.	1.3	9
6	RHEED intensity oscillation of C60 layer epitaxial growth. Journal of Crystal Growth, 2009, 311, 2227-2231.	1.5	8
7	Growth of CuGaSe ₂ Layers on Closely Lattice-Matched GaAs Substrates by Migration-Enhanced Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 125502.	1.5	8
8	Photoluminescence study of Si doped and undoped Chalcopyrite CuGaSe ₂ thin films. Applied Physics A: Materials Science and Processing, 2013, 113, 257-261.	2.3	8
9	Study of free GaAs surfaces using a back-gated undoped GaAs/AlGaAs heterostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 663-666.	2.7	7
10	Investigation of C60 Epitaxial Growth Mechanism on GaAs Substrates. Japanese Journal of Applied Physics, 2009, 48, 025502.	1.5	7
11	Characteristics of CuGaSe ₂ layers grown on GaAs substrates. Journal of Crystal Growth, 2013, 378, 154-157.	1.5	7
12	Study of single crystal CuInSe ₂ thin films and CuGaSe ₂ /CuInSe ₂ single quantum well grown by molecular beam epitaxy. Journal of Crystal Growth, 2015, 425, 203-206.	1.5	7
13	Characteristics of multivalent impurity doped C60 films grown by MBE. Journal of Crystal Growth, 2007, 301-302, 687-691.	1.5	6
14	Effect of surface Ga accumulation on the growth of GaN by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 342-346.	0.8	6
15	High absorption efficiency of AlGaAs/GaAs superlattice solar cells. Japanese Journal of Applied Physics, 2015, 54, 052301.	1.5	5
16	Electrical Spin Injection from Ferromagnetic Metals into GaAs. , 2002, , 95-106.		5
17	Effect of Excitons in AlGaAs/GaAs Superlattice Solar Cells. Japanese Journal of Applied Physics, 2011, 50, 052302.	1.5	4
18	High-Absorption-Efficiency Superlattice Solar Cells by Excitons. Japanese Journal of Applied Physics, 2013, 52, 112302.	1.5	4

#	ARTICLE	IF	CITATIONS
19	Excitonic absorption on AlGaAs/GaAs superlattice solar cells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 330-333.	0.8	2
20	Backgated layers and nanostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 11, 155-160.	2.7	1
21	Transport characteristics of electrons in weak short-period two-dimensional potential arrays. <i>Applied Physics Letters</i> , 2001, 79, 427-429.	3.3	1
22	Field Effect of Photoluminescence from Excitons Bound to Nitrogen Atom Pairs in GaAs. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 5503-5506.	1.5	1
23	Optical Properties of Amorphous and Nanostructure Si/SiO ₂ /Quantum Wells. <i>Journal of Nano Research</i> , 0, 26, 59-62.	0.8	1
24	Optical properties of Al Ga ^{1-x} As/GaAs superlattice solar cells. <i>Journal of Crystal Growth</i> , 2015, 425, 333-336.	1.5	1
25	Electric Field Induced Recombination Centers in GaAs. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 1622-1625.	1.5	0
26	Magnetic and Electric Field Effects of Photoluminescence of Excitons Bound to Nitrogen Atom Pairs in GaAs. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L756-L758.	1.5	0
27	Magnetic Properties of Multiply Mn δ -Doped GaAs. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 113001.	1.5	0